

9097250 TOSHIBA (DISCRETE/OPTO)

99D 16898 DT-39-11



SEMICONDUCTOR

TECHNICAL DATA

TOSHIBA FIELD EFFECT TRANSISTOR

YTF833

SILICON N CHANNEL MOS TYPE

(π-MOS II)

HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS.
CHOPPER REGULATOR, DC-DC CONVERTER AND MOTOR
DRIVE APPLICATIONS.

FEATURES:

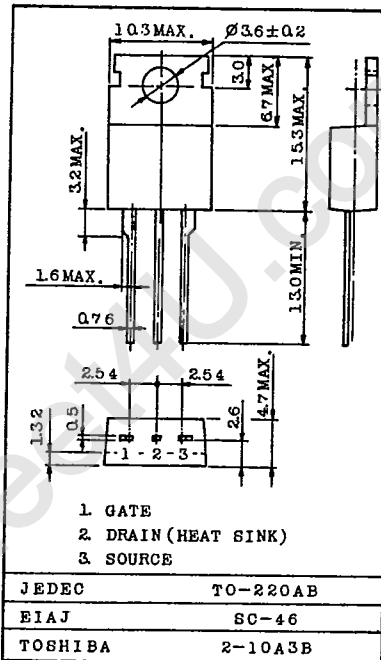
- Low Drain-Source ON Resistance : $R_{DS(ON)} = 1.5\Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 3.25S$ (Typ.)
- Low Leakage Current : $I_{GSS} = \pm 500nA$ (Max.) @ $V_{GS} = \pm 20V$
 $I_{DSS} = 250\mu A$ (Max.) @ $V_{DS} = 450V$
- Enhancement-Mode : $V_{th} = 2.0 \sim 4.0V$ @ $V_{DS} = V_{GS}, I_D = 250\mu A$

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		V_{DSX}	450	V
Drain-Gate Voltage ($R_{GS} = 1M\Omega$)		V_{DGR}	450	V
Gate-Source Voltage		V_{GSS}	± 20	V
Drain Current	DC ($T_c = 25^\circ C$)	I_D	4	A
	DC ($T_c = 100^\circ C$)	I_D	2.5	
	Pulse	I_{DP}	16	
Inductive Current (Clamped)		I_{LP}	16	A
Drain Power Dissipation ($T_c = 25^\circ C$)		P_D	75	W
Channel Temperature		T_{ch}	150	$^\circ C$
Storage Temperature Range		T_{stg}	$-55 \sim 150$	$^\circ C$

INDUSTRIAL APPLICATIONS

Unit in mm



Weight : 1.9g

THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Junction to Case	$R_{th(j-c)}$	1.67	$^\circ C/W$
Thermal Resistance, Junction to Ambient	$R_{th(j-a)}$	80	$^\circ C/W$
Maximum Lead Temperature for Soldering Purposes (1.6mm from case for 10 seconds)	T_L	300	$^\circ C$

TOSHIBA CORPORATION

GT1A2

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ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Gate Leakage Current	IGSS	V _{GS} =±20V, V _{DS} =0V	-	-	±500	nA	
Drain Cut-off Current	IDSS	V _{DS} =450V, V _{GS} =0V, T _c =25°C	-	-	250	μA	
Drain-Source Breakdown Voltage	V _{(BR)DSS}	I _D =250μA, V _{GS} =0V	450	-	-	V	
Gate Threshold Voltage	V _{th}	V _{DS} =V _{GS} , I _D =250μA	2.0	-	4.0	V	
Forward Transfer Admittance	Y _{fs}	V _{DS} =10V, I _D =2.5A	2.5	3.25	-	S	
On-State Drain Current	I _{D(ON)}	V _{DS} =10V, V _{GS} =10V	4	-	-	A	
Drain-Source ON Resistance	R _{DS(ON)}	I _D =2.5A, V _{GS} =10V	-	1.5	2.0	Ω	
Drain-Source ON Voltage	V _{DS(ON)}	I _D =4.5A, V _{GS} =10V	-	7.4	9.4	V	
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, f=1MHz	-	600	800	pF	
Reverse Transfer Capacitance	C _{rss}		-	40	60	pF	
Output Capacitance	C _{oss}		-	150	200	pF	
Switching Time	Rise Time	t _r		-	15	30	ns
	Turn-on Time	t _{on}		-	30	60	ns
	Fall Time	t _f		-	15	30	ns
	Turn-off Time	t _{off}		-	40	85	ns
Total Gate Charge (Gate-Source Plus Gate-Drain)	Q _g	V _{GS} =10V, I _D =6A, V _{DS} =360V	-	22	30	nC	
Gate Source Charge	Q _{gs}		-	11	-	nC	
Gate-Drain ("Miller") Charge	Q _{gd}		-	11	-	nC	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Source Current	I _S	—	-	-	4	A
Pulse Source Current	I _{SP}	—	-	-	16	A
Diode Forward Voltage	V _{SD}	I _S =4A, V _{GS} =0V, T _c =25°C	-	-	1.5	V
Reverse Recovery Time	t _{rr}	T _j =150°C, I _F =4.5A,	-	800	-	ns
Reverse Recovered Charge	Q _{rr}	dI _F /dt=100A/μs	-	4.6	-	μC

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